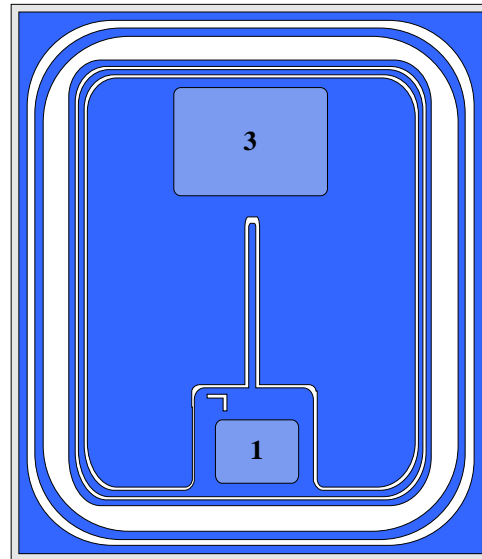


3VD379500YL HIGH VOLTAGE MOSFET CHIPS
DESCRIPTION

- Ø 3VD379500YL is a High voltage N-Channel enhancement mode power MOS-FET chip fabricated in advanced silicon epitaxial planar technology;
- Ø Advanced termination scheme to provide enhanced voltage-blocking capability;
- Ø Avalanche Energy Specified;
- Ø Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode;
- Ø The chips may packaged in TO-220 type;
- Ø The packaged product is widely used in AC-DC power suppliers, DC-DC converters and H-bridge PWM motor drivers;
- Ø Die size: 3.8mm*2.8mm;
- Ø Chip Thickness: 300±20µm;
- Ø Top metal : Al, Backside Metal : Ag.



PAD1:GATE PAD3:SOURCE

CHIP TOPOGRAPHY

ABSOLUTE MAXIMUM RATINGS (T_{amb}=25°C)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V _{DS}	500	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current	I _D	5.5	A
Power Dissipation (TO-220 Package)	P _D	74	W
Operation Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain -Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250µA	500	-	-	V
Gate Threshold Voltage	V _{TH}	V _{GS} = V _{DS} , I _D =250µA	2	-	4	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =500V, V _{GS} =0V	-	-	1	µA
Static Drain- Source On State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =2.7A	-	-	1.5	Ω
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Source-Drain Diode Forward on Voltage	V _{FSD}	I _S =4.5A, V _{GS} =0V	-	-	1.6	V